

N-Channel 100 V (D-S) MOSFET

| MOSFET PRODUCT SUMMARY | | | |
|------------------------|----------------------------------|---------------------------------|-----------------------|
| V _{DS} (V) | R _{DS(on)} (Ω) Max. | I _D (A) ^a | Q _g (Typ.) |
| 100 | 0.126 at V _{GS} = 10 V | 3.8 | 2.9 nC |
| | 0.147 at V _{GS} = 6 V | 3.5 | |
| | 0.189 at V _{GS} = 4.5 V | 3.1 | |

FEATURES

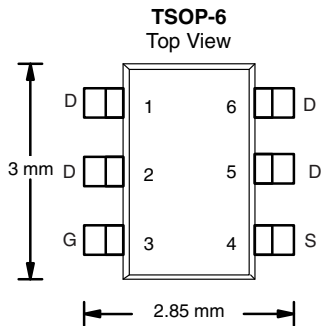
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

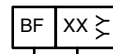
APPLICATIONS

- DC/DC Converters / Boost Converters
- Load Switch
- LED Backlighting in LCD TVs
- Power Management for Mobile Computing



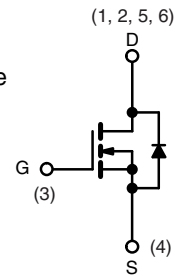
Ordering Information:
Si3474DV-T1-GE3 (Lead (Pb)-free and Halogen-free)

Marking Code



Lot Traceability
and Date Code

Part # Code



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | |
|---|-----------------------------------|------------------------|---------------------|
| Parameter | Symbol | Limit | Unit |
| Drain-Source Voltage | V _{DS} | 100 | V |
| Gate-Source Voltage | V _{GS} | ± 20 | |
| Continuous Drain Current (T _J = 150 °C) | I _D | T _C = 25 °C | 3.8 |
| | | T _C = 70 °C | 3 |
| | | T _A = 25 °C | 2.8 ^{b, c} |
| | | T _C = 70 °C | 2.3 ^{b, c} |
| Pulsed Drain Current (t = 100 μs) | I _{DM} | 14 | A |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | |
| | | T _A = 25 °C | 1.7 ^{b, c} |
| Single Pulse Avalanche Current | L = 0.1 mH I _{AS} | 2.5 | mJ |
| Single Pulse Avalanche Energy | E _{AS} | 0.31 | |
| Maximum Power Dissipation | P _D | T _C = 25 °C | 3.6 |
| | | T _C = 70 °C | 2.33 |
| | | T _A = 25 °C | 2 ^{b, c} |
| | | T _A = 70 °C | 1.3 ^{b, c} |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 150 | °C |

| THERMAL RESISTANCE RATINGS | | | | |
|---|-------------------|---------|---------|------|
| Parameter | Symbol | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient ^{b, d} | R _{thJA} | 50 | 62.5 | °C/W |
| Maximum Junction-to-Foot (Drain) | R _{thJF} | 28 | 35 | |

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 110 °C/W.

| MOSFET SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | |
|--|--------------------------------------|---|------|-------|-------|-------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | 100 | | | V |
| V _{DS} Temperature Coefficient | ΔV _{DS} /T _J | I _D = 250 μA | | 59 | | mV/°C |
| V _{GS(th)} Temperature Coefficient | ΔV _{GS(th)} /T _J | | | - 4.8 | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | 1.2 | | 3 | V |
| Gate-Source Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 100 V, V _{GS} = 0 V | | | - 1 | μA |
| | | V _{DS} = 100 V, V _{GS} = 0 V, T _J = 55 °C | | | - 10 | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} ≥ 5 V, V _{GS} = 10 V | 5 | | | A |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 10 V, I _D = 2 A | | 0.102 | 0.126 | Ω |
| | | V _{GS} = 6 V, I _D = 1 A | | 0.120 | 0.147 | |
| | | V _{GS} = 4.5 V, I _D = 1 A | | 0.135 | 0.189 | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = 20 V, I _D = 2 A | | 5 | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz | | 196 | | pF |
| Output Capacitance | C _{oss} | | | 67 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 14 | | |
| Total Gate Charge | Q _g | V _{DS} = 50 V, V _{GS} = 10 V, I _D = 2.2 A | | 5.2 | 10.4 | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} = 50 V, V _{GS} = 4.5 V, I _D = 2.2 A | | 2.9 | 5.8 | |
| Gate-Drain Charge | Q _{gd} | | | 1 | | |
| Gate Resistance | R _g | f = 1 MHz | 0.9 | 4.3 | 8.6 | Ω |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 50 V, R _L = 27.7 Ω I _D = 1.8 A, V _{GEN} = 4.5 V, R _g = 1 Ω | | 40 | 60 | ns |
| Rise Time | t _r | | | 68 | 102 | |
| Turn-Off Delay Time | t _{d(off)} | | | 14 | 21 | |
| Fall Time | t _f | | | 20 | 30 | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 50 V, R _L = 27.7 Ω I _D = 1.8 A, V _{GEN} = 10 V, R _g = 1 Ω | | 8 | 16 | ns |
| Rise Time | t _r | | | 10 | 20 | |
| Turn-Off Delay Time | t _{d(off)} | | | 10 | 20 | |
| Fall Time | t _f | | | 7 | 14 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | - 2.1 | A |
| Pulse Diode Forward Current (t = 100 μs) | I _{SM} | | | | - 8 | |
| Body Diode Voltage | V _{SD} | I _S = 1.8 A | | - 0.8 | - 1.2 | V |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 1.8 A, di/dt = 100 A/μs, T _J = 25 °C | | 23 | 35 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | 21 | 32 | nC |
| Reverse Recovery Fall Time | t _a | | | 17 | | ns |
| Reverse Recovery Rise Time | t _b | | | 6 | | |

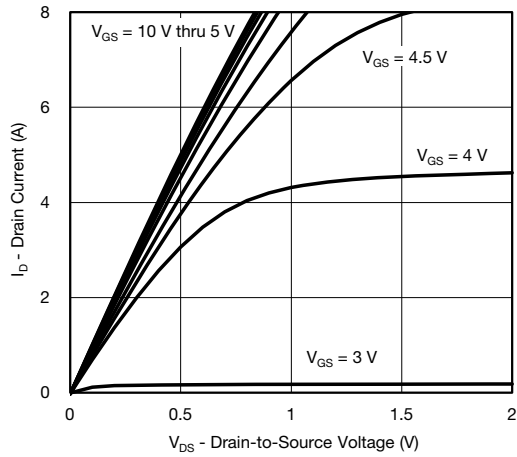
Notes:

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.

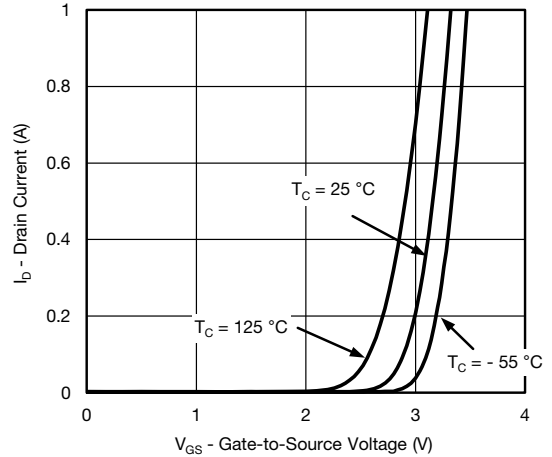
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

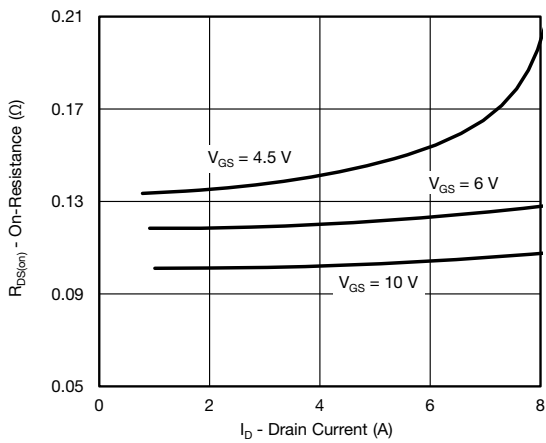
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



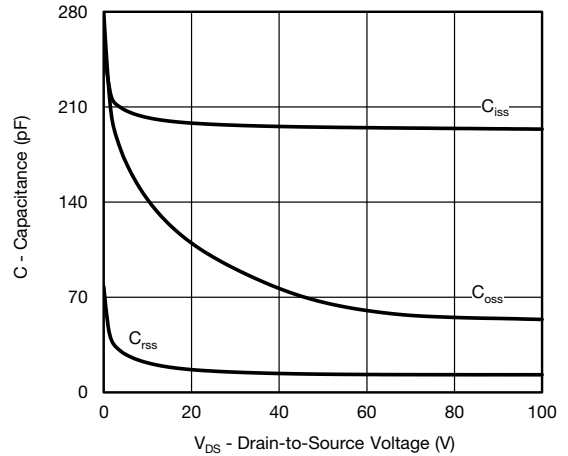
Output Characteristics



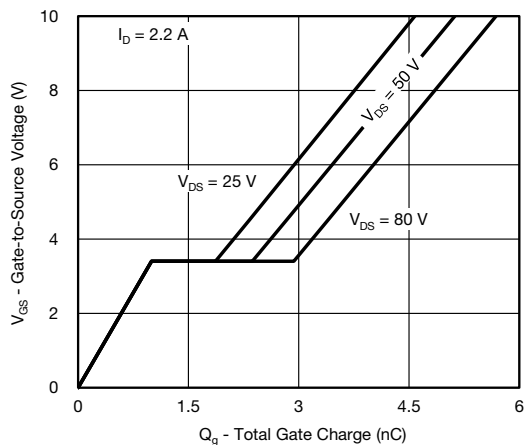
Transfer Characteristics



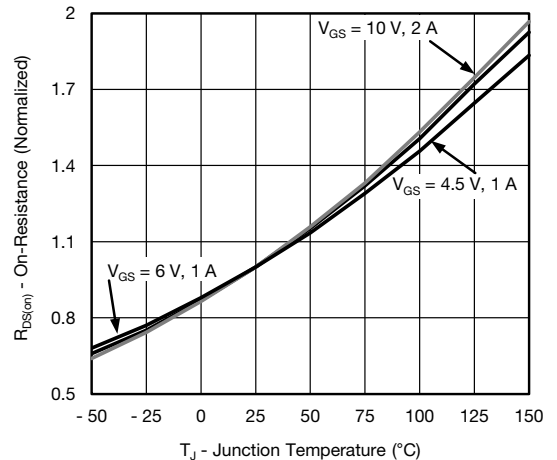
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

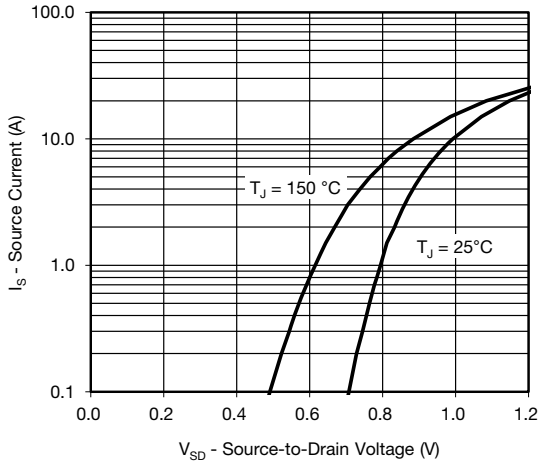


Gate Charge

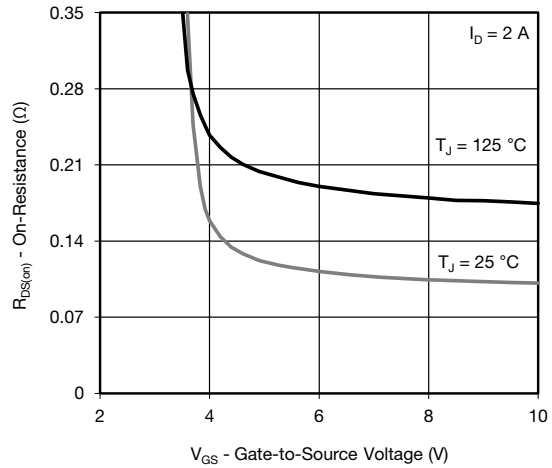


On-Resistance vs. Junction Temperature

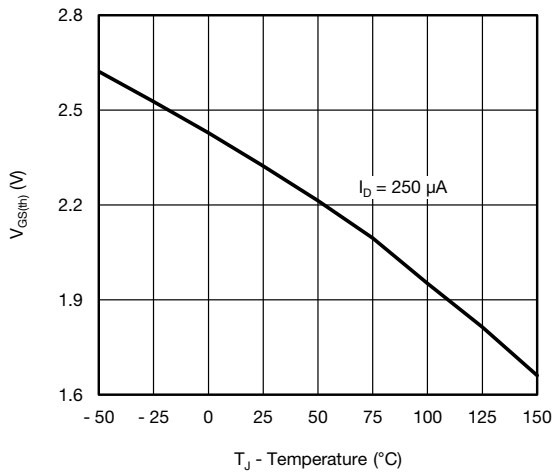
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



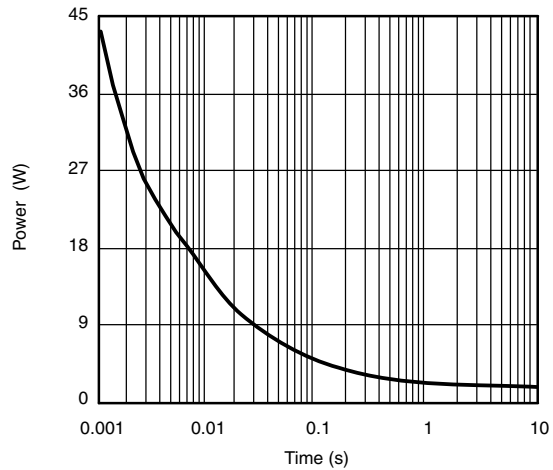
Source-Drain Diode Forward Voltage



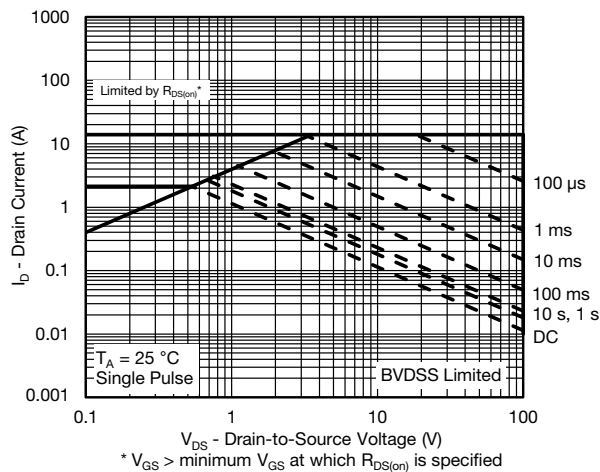
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

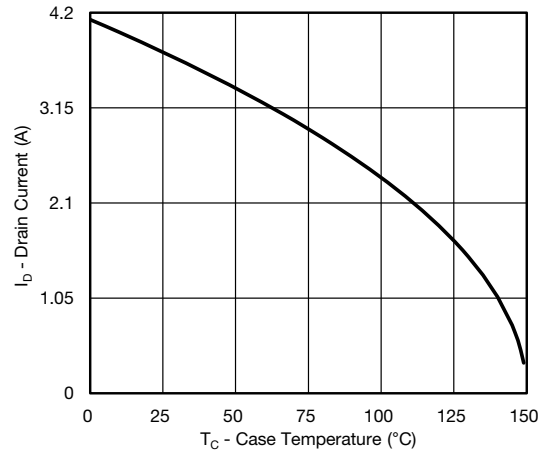


Single Pulse Power

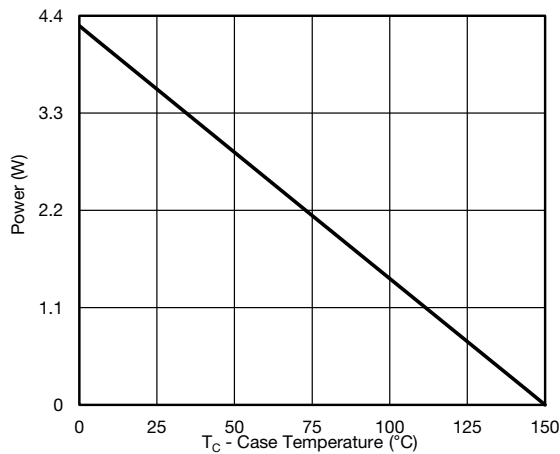


Safe Operating Area

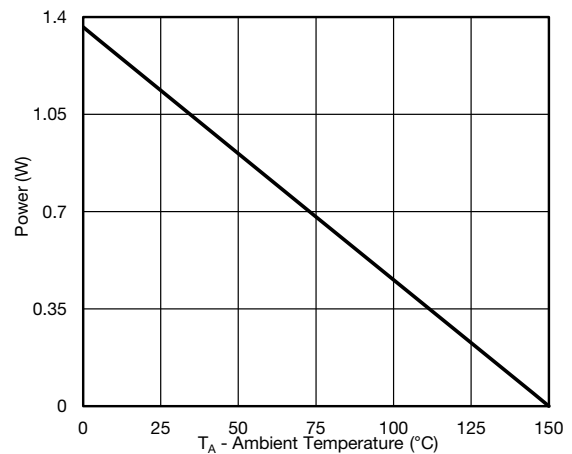
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



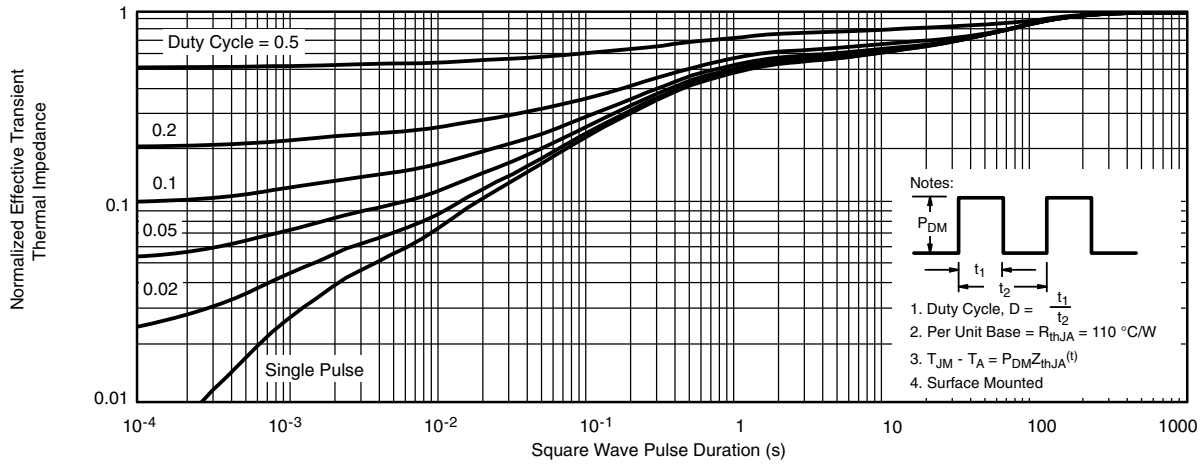
Power, Junction-to-Foot



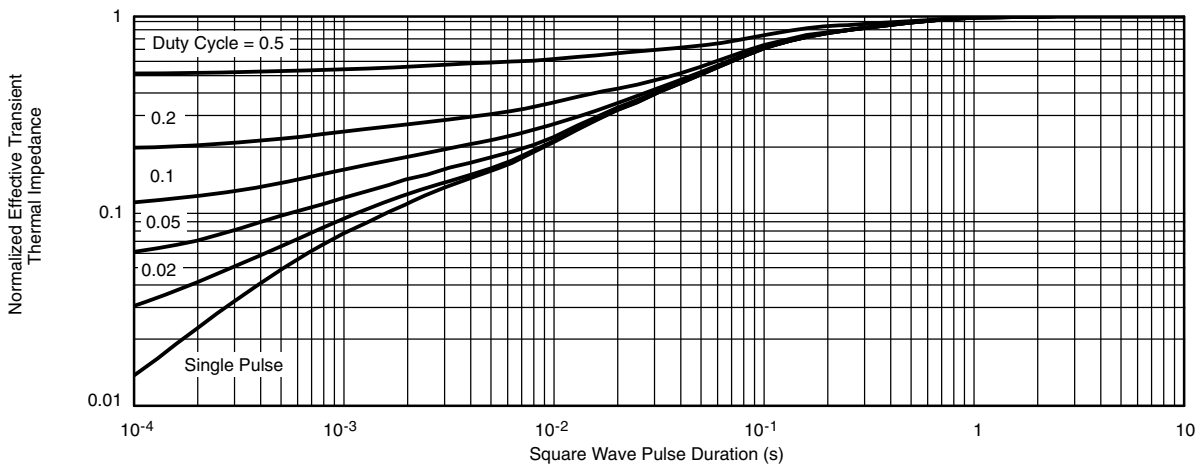
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C



5-LEAD TSOP

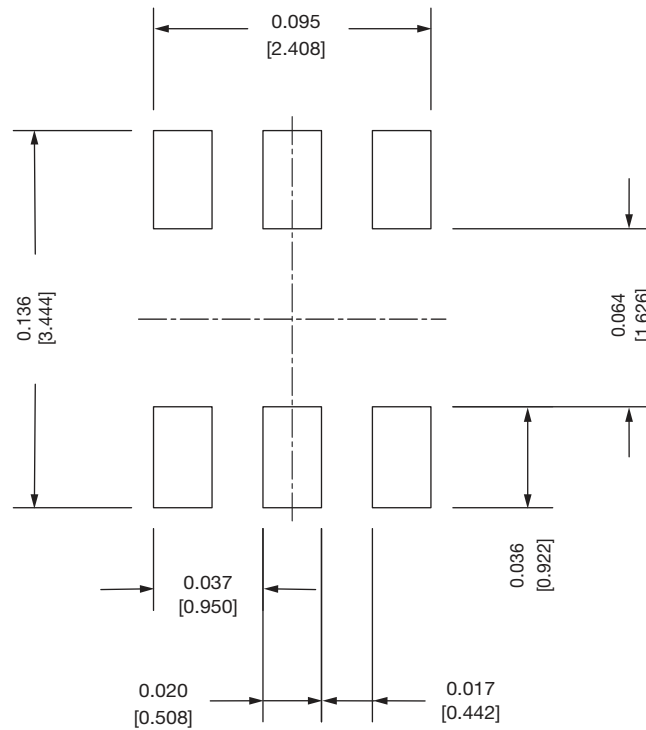
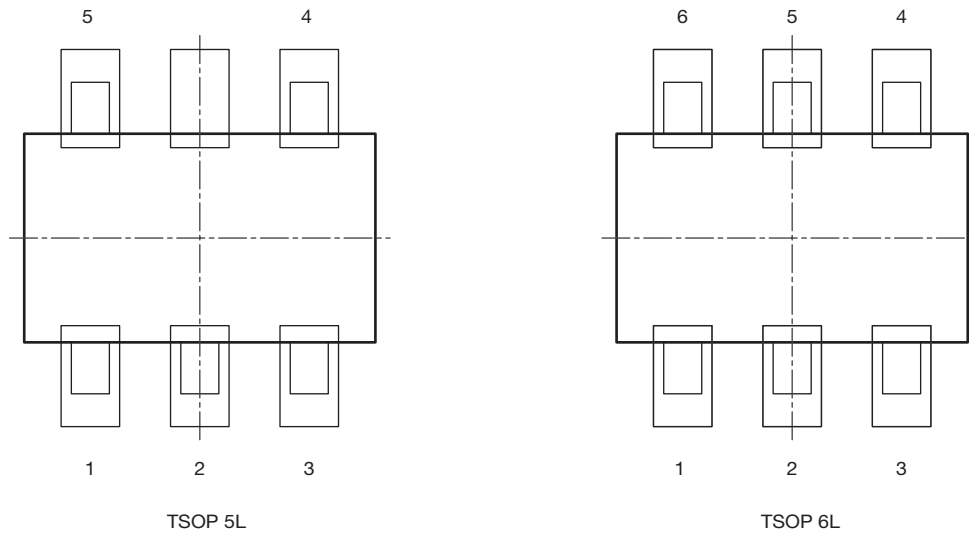


6-LEAD TSOP



| Dim | MILLIMETERS | | | INCHES | | |
|--------------------------------|-------------|------|------|------------|-------|-------|
| | Min | Nom | Max | Min | Nom | Max |
| A | 0.91 | - | 1.10 | 0.036 | - | 0.043 |
| A₁ | 0.01 | - | 0.10 | 0.0004 | - | 0.004 |
| A₂ | 0.90 | - | 1.00 | 0.035 | 0.038 | 0.039 |
| b | 0.30 | 0.32 | 0.45 | 0.012 | 0.013 | 0.018 |
| c | 0.10 | 0.15 | 0.20 | 0.004 | 0.006 | 0.008 |
| D | 2.95 | 3.05 | 3.10 | 0.116 | 0.120 | 0.122 |
| E | 2.70 | 2.85 | 2.98 | 0.106 | 0.112 | 0.117 |
| E₁ | 1.55 | 1.65 | 1.70 | 0.061 | 0.065 | 0.067 |
| e | 0.95 BSC | | | 0.0374 BSC | | |
| e₁ | 1.80 | 1.90 | 2.00 | 0.071 | 0.075 | 0.079 |
| L | 0.32 | - | 0.50 | 0.012 | - | 0.020 |
| L₁ | 0.60 Ref | | | 0.024 Ref | | |
| L₂ | 0.25 BSC | | | 0.010 BSC | | |
| R | 0.10 | - | - | 0.004 | - | - |
| θ | 0° | 4° | 8° | 0° | 4° | 8° |
| θ₁ | 7° Nom | | | 7° Nom | | |
| ECN: C-06593-Rev. I, 18-Dec-06 | | | | | | |
| DWG: 5540 | | | | | | |

Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022
 DWG: 3010



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